Number	15 15 22 22 22
14:10	15 15 22 22 22
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT 2002/05/14:58  - 1 "5612249".PN. USPAT 2002/05/14:58  - 1 "5637514".PN. USPAT 2002/05/14:58  - 1 "5798550".PN. USPAT 2002/05/14:59  - 1 "6015736".PN. USPAT 2002/05/14:59  - 3 ("5306655").PN. USPAT 2002/05/15:00  - 3 ("5306655").PN. USPAT 2002/05/15:00  - 3 ("5306758").PN. USPAT;	15 22 22 22
TEM_TDB   Consider near spacer near 6 nitride and (mosfet or mos adj device or field adj effect adj transistor).ti,ab,clm.   TEM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   TEM_TDB   USPAT   USPAT;   USPAT;   USPAT;   USPAT;   USPAT;   USPAT;   USPAT   U	15 22 22 22
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(mosfet or mos adj device or field adj effect adj transistor).ti,ab,clm.	15 22 22 22
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- 5 272,968.ap. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT 2002/05/ - 1 "5612249".PN. USPĀT 2002/05/ - 1 "5637514".PN. USPĀT 2002/05/ - 1 "5798550".PN. USPĀT 2002/05/ - 1 "6015736".PN. USPĀT 2002/05/ - 3 ("5306655").PN. USPĀT 2002/05/ - 3 ("5360758").PN. USPĀT 2002/05/ - 3 ("5360758").PN. USPĀT 2002/05/ - 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or pmosfet) uspāt; USPĀCPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; USPĀCPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; USPĀCPUB; US	22 22 22
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/14:59 2002/05/15:43	22 22 22
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- 1 "5637514".PN. USPAT 2002/05/14:59 - 1 "5798550".PN. USPAT 2002/05/14:59 - 1 "6015736".PN. USPAT 2002/05/14:59 - 3 ("5306655").PN. USPAT; U	22
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3 ("5306655").PN.   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   DERWENT;   IBM_TDB   USPAT;	c. 1.
- 3 ("5306655").PN.  - 3 ("5360758").PN.  - 3 ("5360758").PN.  - 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN.  USPAT; 2002/05/3  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  USPAT; US-PGPUB; O9:41  USPAT; US-PGPUB; O9:41  USPAT; 2002/05/3	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; transistor or fet or mos or mos adj fet or mosfet or mosfet)  - 3 ("5382533").PN. USPAT; 2002/05/2	22
- 301 ("5360758").PN.  - 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN.  DERWENT; IBM_TDB USPAT; 2002/05/3	
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3 ("5360758").PN.  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; USPAT; US-PGPUB; EPO; JPO; USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; DERWENT; OF mosfet or mos or mos adj fet or mosfet or nmosfet or nmosfet or nmosfet or nmosfet or nmosfet or nmosfet)  USPAT;	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  ("5382533").PN.  US-PGPUB; EPO; JPO; DERWENT; DERWENT; IBM_TDB  USPAT; 2002/05/2	
- 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN.  EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  USPAT; 2002/05/2	22
- 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN.  DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB  USPAT; 2002/05/2	
- 301 ((side adj wall or sidewall or side-wall) adj spacer near6 nitride) and 257/\$6.ccls. and (field adj effect adj transistor or fet or mos or mos adj fet or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN.  IBM_TDB USPAT; 2002/05/2	
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transistor or fet or mos or mos adj fet or mosfet or nmosfet or nmosfet or nmosfet or pmosfet)  - 3 ("5382533").PN. USPAT; 2002/05/2	
or mosfet or nmos or pmos or nmosfet or pmosfet)  - 3 ("5382533").PN. USPAT; 2002/05/2	
pmosfet) - 3 ("5382533").PN. USPAT; 2002/05/2	
- 3 ("5382533").PN. USPAT; 2002/05/2	
	:2
EPO; JPO;	
DERWENT;	
. IBM TDB	
- 3 ("5679968").PN. USPAT; 2002/05/2	22
US-PGPUB; 17:52	
EPO; JPO;	
DERWENT;	
-   IBM_TDB   USPAT: 2002/05/3	
- 3 ("5714413").PN. USPĀT; 2002/05/2 US-PGPUB; 17:53	. 2
US-PGPOB; 17:53 EPO; JPO;	
DERWENT;	
IBM TDB	
- 0 ("ep-621632\$-\$.did.").PN. USPAT; 2002/05/2	
US-PGPUB; 17:53	:2
EPO; JPO;	:2
DERWENT;	:2
IBM_TDB	?2
0 ("ep-621632\$-\$.did.").PN. USPAT; 2002/05/2	
US-PGPUB; 17:53	
EPO; JPO; DERWENT;	
IBM TDB	
- 0 rajeevakumar.in. and dram adj cell adj EPO 2002/05/2	
structure 17:55	22

_	6	rajeevakumar.in. and dram adj cell adj	USPAT;	2002/05/22
		structure	US-PGPUB;	17:55
			EPO; JPO;	
	1		DERWENT;	
		(#5.6100.40#)	IBM_TDB	2002/05/22
-	3	("5612249").PN.	USPAT;	2002/05/23
			US-PGPUB; EPO; JPO;	10:42
			DERWENT;	
			IBM TDB	
! <u>_</u>	0	earom and selection same transistor same	USPAT;	2002/05/23
-	"	dram	US-PGPUB;	10:43
		diam	EPO; JPO;	10.13
			DERWENT;	
			IBM TDB	
_	27	earom and transistor same dram	USPAT;	2002/05/23
			US-PGPUB;	10:44
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	6	earom and transistor same dram.ti,ab.	USPĀT;	2002/05/23
			US-PGPUB;	10:45
	į		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	109394	earom.ti,ab. and dram.ti,ab. and	USPAT;	2002/05/23
		257/\$6.ccls. or 438/\$6.ccls.	US-PGPUB;	10:46
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	earom.ti,ab. and dram.ti,ab.	USPAT;	2002/05/23
			US-PGPUB;	10:47
	1		EPO; JPO;	
			DERWENT;	
	107	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2002/05/23
-	187	•	USPAT; US-PGPUB;	10:49
	1	mosfet) near12 dram	EPO; JPO;	10.49
			DERWENT;	
			IBM TDB	
_	44	(selection near6 (transistor or fet or	USPAT;	2002/05/23
		mosfet) near6 dram) and (257/\$6.ccls. or	US-PGPUB;	12:09
		438/\$6.ccls.)	EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
-	3	("5854500").PN.	USPAT;	2002/05/23
			US-PGPUB;	12:14
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0000 (07 (00
-	2	("6037639").PN.	USPAT;	2002/05/23
			US-PGPUB;	13:57
			EPO; JPO;	
			DERWENT;	
	1000	(257/206) CCTS	IBM_TDB	2002/05/23
-	1962	(257/296).CCLS.	USPAT;	2002/05/23
			US-PGPUB; EPO; JPO;	12.20
			DERWENT;	
			IBM TDB	
<b> </b> _	1041	(257/401).CCLS.	USPAT;	2002/05/23
	1041	/20./ 102/ 1020	US-PGPUB;	15:08
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
1 -	432	(257/410).CCLS.	USPAT;	2002/05/23
		, ,	US-PGPUB;	15:08
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

_	2	("5885553").PN.	USPAT;	2002/11/06
			US-PGPUB;	10:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	. 2	("5612249").PN.	USPAT;	2002/11/06
			US-PGPUB;	12:04
			EPO; JPO;	12.01
			DERWENT;	
			IBM TDB	
_	1 0	(side adj wall or sidewall) near12 gate	USPAT;	2002/11/06
		adj oxide near12 silicon adj nitride adj	US-PGPUB;	12:06
		spacer	EPO; JPO;	12:06
			DERWENT;	
				1
_	15	(side adj wall or sidewall) near12 gate	IBM_TDB	0000 (55:455
	1	adj oxide near12 silicon adj nitride	USPAT;	2002/11/06
		adj oxide heariz silicon adj nitride	US-PGPUB;	12:07
			EPO; JPO;	1
			DERWENT;	
_	147	ovádená sp. odá hovot sp. ovat s	IBM_TDB	
	14/	oxidation adj barrier near4 oxide	USPAT;	2002/11/06
			US-PGPUB;	13:06
			EPO; JPO;	
			DERWENT;	
	001	(140.7	IBM_TDB	
-	201	(MOS or MOSFET).ti,ab,clm. and silicon	USPAT;	2002/11/06
		adj nitride near4 (sidewall or side adj	US-PGPUB;	13:09
		wall) near4 spacer	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3702	((257/296) or (257/401) or	USPAT;	2002/11/06
		(257/410)).CCLS.	US-PGPUB;	16:38
	]		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(((257/296) or (257/401) or	USPAT;	2002/11/06
		(257/410)).CCLS.) and "bird's beak" near4	US-PGPUB;	16:39
	į į	gate near4 underneath and silicon adj	EPO; JPO;	
		nitride	DERWENT;	
			IBM TDB	